

# Search History (16 pp.) 8/17/05

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	5	"773333".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/17 12:18
L3	1	(low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align\$3 self-aligned self-alignment selfalign\$3 selfalignment) and overlap near4 ("mu.m" micron ">ANG." Angstrom Angstroem)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 12:20
L4	1	(low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align\$3 self-aligned self-alignment selfalign\$3 selfalignment) and overlap near4 ("mu.m" micron "ANG." Angstrom Angstroem)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 12:21
L5	1	(low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align\$3 self-aligned self-alignment selfalign\$3 selfalignment) and (overlapping overlapped overlap) near4 ("mu. m" micron "ANG." Angstrom Angstroem)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 12:22
L6	14	(tft thin adj film adj transistor) and (self-align\$3 self-aligned self-alignment selfalign\$3 selfalignment) and (overlapping overlapped overlap) near4 ("mu. m" micron "ANG." Angstrom Angstroem)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 12:59
L7	2219	(self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj dran)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:00
L8	2219	(self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:00
L9	1012	(self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain). ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:00

L10	136	(self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain). ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:05
L11	5	(self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain). ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm. and hot adj electron adj effect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:05
L12	9	(self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain). ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm. and hot adj electron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:05
S1	2	jp-05335573\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 08:24
S2	0	jp-200345892\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S3	2	jp-2003045892\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S4	2	jp-08250742\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S5	2	jp-11307777\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S6	2	jp-2000353811\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:41

S7	10	S1 S2 S3 S4 S5 S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 17:11
S8	5	"773333".ap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:44
S9	18	(tft thin adj film adj transistor) and overlap near6 ("low" "high") near2 voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:05
S10	4455	"low" near2 voltage and "high" near2 voltage and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:09
S11	80	"low" near2 voltage near20 gate adj (insulation insulating oxide) and "high" near2 voltage near20 gate adj (insulation insulating oxide) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:10
S12	5683	((257/59) or (257/72) or (257/351) or (257/355) or (257/356) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395) or (257/406)).CCLS	US-PGPUB; USPAT	OR	OFF	2005/03/05 17:39
S13	19	S12 and gate adj insulat\$3.clm. and "high" adj2 voltage.clm. and "low" adj2 voltage.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:44
S14	133	(257/406).CCLS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 17:44

S15	42	(US-20040195568-\$ or US-20040046174-\$ or US-20030025127-\$ or US-20020149056-\$ or US-20020135554-\$ or US-20020042170-\$ or US-20020041350-\$ or US-20020030190-\$ or US-20020024048-\$ or US-20010013912-\$ or US-20010000755-\$ or US-20040026750-\$ or US-20020084490-\$).did. or (US-6856360-\$ or US-6657228-\$ or US-6452211-\$ or US-6426787-\$ or US-6420988-\$ or US-6400434-\$ or US-6384886-\$ or US-6368904-\$ or US-6316787-\$ or US-6303963-\$ or US-6294815-\$ or US-6165824-\$ or US-6163055-\$ or US-6115094-\$ or US-5528056-\$ or US-6597046-\$ or US-5468987-\$).did. or (JP-2003045892-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$ or JP-54015678-\$ or JP-02222169-\$).did. or (US-20030025127-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:05
S16	317	(257/391).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 18:06

S17	46	(US-20040195568-\$ or US-20040046174-\$ or US-20030025127-\$ or US-20020149056-\$ or US-20020135554-\$ or US-20020042170-\$ or US-20020041350-\$ or US-20020030190-\$ or US-20020024048-\$ or US-20010013912-\$ or US-20010000755-\$ or US-20040026750-\$ or US-20020084490-\$ or US-20020190343-\$ or US-20020117723-\$).did. or (US-6856360-\$ or US-6657228-\$ or US-6452211-\$ or US-6426787-\$ or US-6420988-\$ or US-6400434-\$ or US-6384886-\$ or US-6368904-\$ or US-6316787-\$ or US-6303963-\$ or US-6294815-\$ or US-6165824-\$ or US-6163055-\$ or US-6115094-\$ or US-5528056-\$ or US-6597046-\$ or US-5468987-\$ or US-6541823-\$ or US-5576556-\$).did. or (JP-2003045892-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$ or JP-54015678-\$ or JP-02222169-\$).did. or (US-20030025127-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:33
S18	5	S17 and double adj gate	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:35
S19	2	S17 and ((additional extra second double) adj gate sub-gate) near5 (withstand break-down breakdown) near2 voltage	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:47
S20	326	(257/392).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 18:57
S21	138	(257/270).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 18:59
S22	264	(257/346).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 19:06
S23	159	(257/387).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/08/16 12:38

S24	5	"low" near1 voltage near10 (tft thin adj film adj transistor) near10 (self-alignment selfaligned overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 19:14
-----	---	---	---	----	-----	------------------

S25	82	(US-20040195568-\$ or US-20040046174-\$ or US-20030025127-\$ or US-20020149056-\$ or US-20020135554-\$ or US-20020042170-\$ or US-20020041350-\$ or US-20020030190-\$ or US-20020024048-\$ or US-20010013912-\$ or US-20010000755-\$ or US-20040026750-\$ or US-20020084490-\$ or US-20020190343-\$ or US-20020117723-\$ or US-20030132500-\$).did. or (US-6856360-\$ or US-6657228-\$ or US-6452211-\$ or US-6426787-\$ or US-6420988-\$ or US-6400434-\$ or US-6384886-\$ or US-6368904-\$ or US-6316787-\$ or US-6303963-\$ or US-6294815-\$ or US-6165824-\$ or US-6163055-\$ or US-6115094-\$ or US-5528056-\$ or US-6597046-\$ or US-5468987-\$ or US-6541823-\$ or US-5576556-\$ or US-6847080-\$ or US-6847088-\$ or US-6853030-\$ or US-6770940-\$ or US-6653694-\$ or US-6646313-\$ or US-6627963-\$).did. or (US-6593191-\$ or US-6586805-\$ or US-6579736-\$ or US-6563182-\$ or US-6559489-\$ or US-6492690-\$ or US-6380590-\$ or US-6333541-\$ or US-6300663-\$ or US-6271572-\$ or US-6267479-\$ or US-6265739-\$ or US-6251732-\$ or US-6198140-\$ or US-6191460-\$ or US-6175138-\$ or US-6166417-\$ or US-6093594-\$ or US-5696400-\$ or US-5654577-\$ or US-4205330-\$ or US-4183040-\$ or US-4104784-\$ or US-4085498-\$ or US-6157062-\$ or US-6064096-\$ or US-5736750-\$).did. or (US-6469348-\$).did. or (JP-2003045892-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$ or JP-54015678-\$ or JP-02222169-\$).did. or (US-20030025127-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 19:19
-----	----	---	--	----	-----	------------------

S26	10	(JP-05335573-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-2000353811-\$ or JP-2003045892-\$).did. or (JP-05335573-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-2000353811-\$ or US-20030025127-\$).did.	JPO; DERWENT	OR	OFF	2005/03/05 19:43
S27	1	("6509602").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 19:51
S28	14	S25 and (overlap overlapping) near4 (source drain gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 19:52
S29	1	ikeda.in. and yamazaki.in. and thinner.ab. and gate and pixel and TFT.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 20:16
S30	465	(overlap overlapping) near10 (self-alignment self-aligned) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:34
S31	207	(overlap overlapping) near4 (self-alignment self-aligned) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:34
S32	102	(overlap overlapping) near4 (self-alignment self-aligned) near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:35
S33	22	(overlap overlapping) near4 (self-alignment self-aligned) near4 gate and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:35

S34	82	(US-20010000755-\$ or US-20010013912-\$ or US-20020024048-\$ or US-20020030190-\$ or US-20020041350-\$ or US-20020042170-\$ or US-20020084490-\$ or US-20020117723-\$ or US-20020135554-\$ or US-20020149056-\$ or US-20020190343-\$ or US-20030025127-\$ or US-20030132500-\$ or US-20040026750-\$ or US-20040046174-\$ or US-20040195568-\$).did. or (US-4085498-\$ or US-4104784-\$ or US-4183040-\$ or US-4205330-\$ or US-5468987-\$ or US-5528056-\$ or US-5576556-\$ or US-5654577-\$ or US-5696400-\$ or US-5736750-\$ or US-6064096-\$ or US-6093594-\$ or US-6115094-\$ or US-6157062-\$ or US-6163055-\$ or US-6165824-\$ or US-6166417-\$ or US-6175138-\$ or US-6191460-\$ or US-6198140-\$ or US-6251732-\$ or US-6265739-\$ or US-6267479-\$ or US-6271572-\$ or US-6294815-\$ or US-6300663-\$).did. or (US-6303963-\$ or US-6316787-\$ or US-6333541-\$ or US-6368904-\$ or US-6380590-\$ or US-6384886-\$ or US-6400434-\$ or US-6420988-\$ or US-6426787-\$ or US-6452211-\$ or US-6469348-\$ or US-6492690-\$ or US-6541823-\$ or US-6559489-\$ or US-6563182-\$ or US-6579736-\$ or US-6586805-\$ or US-6593191-\$ or US-6597046-\$ or US-6627963-\$ or US-6646313-\$ or US-6653694-\$ or US-6657228-\$ or US-6770940-\$ or US-6847080-\$ or US-6847088-\$ or US-6853030-\$).did. or (US-6856360-\$).did. or (JP-02222169-\$ or JP-05335573-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-2000353811-\$ or JP-2003045892-\$ or JP-54015678-\$).did. or (JP-05335573-\$ or JP-08250742-\$ or JP-2000353811-\$ or JP-11307777-\$ or US-20030025127-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/06 07:33
-----	----	---	--	----	-----	------------------

S35	3	S34 and yanai.in.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/06 07:40
S36	28	(self-aligned self-aligning self-alignment) near10 ("ANG" "mu.m" micron nm nanometer Angstrom) and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:45
S37	22	(self-aligned self-aligning self-alignment) and LDD and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:55
S38	15	(self-aligned self-aligning self-alignment) and LDD and "low" near1 voltage and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:56
S39	15	(self-aligned self-aligning self-alignment) and LDD and "low" near1 voltage and "high" near1 voltage and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:05
S40	126	LDD near4 "low" near1 voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:05
S41	14	LDD near4 "low" near1 voltage and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:36
S42	5	LDD near4 "low" near1 voltage and tft and (self-aligned self-aligning self-alignment selfaligned selfalignment)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:36
S43	238	second adj electrode near6 TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 10:21

S44	19	split-gate and TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 10:27
S45	131	separate near1 gate and TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 12:22
S46	60	separate near1 gate and TFT	US-PGPUB	OR	OFF	2005/03/06 12:25
S47	654	double adj gate and tft	US-PGPUB	OR	OFF	2005/03/06 12:26
S48	15	double adj gate.ti,ab,clm. and tft	US-PGPUB	OR	OFF	2005/03/06 12:48
S49	2	(overlap overlapping) near6 gate near6 ("."mu.m" ".ANG." nm nanometer micron) and tft.ti,ab, clm.	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:01
S50	7	(overlap overlapping) near6 gate near6 ("."mu.m" ".ANG." nm nanometer micron) and tft	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:36
S51	83	(overlap overlapping) near6 ("."mu. m" ".ANG." nm nanometer micron) and tft	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:36
S52	10	(JP-2003045892-\$ or JP-2000353811-\$ or JP-05335573-\$ or JP-11307777-\$ or JP-08250742-\$).did. or (JP-2000353811-\$ or US-20030025127-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-05335573-\$).did.	JPO; DERWENT	OR	OFF	2005/03/06 13:50
S53	11	(JP-2003045892-\$ or JP-2000353811-\$ or JP-05335573-\$ or JP-11307777-\$ or JP-08250742-\$).did. or (JP-2000353811-\$ or US-20030025127-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-05335573-\$).did	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/06 13:52
S54	266	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/06 13:52
S55	144	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:52

S56	47	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain and tft.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:56
S57	7	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain near6 ("mu.m" nm ".ANG.") and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:57
S58	2	jp-05335573\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 09:53
S59	2	jp-08250742\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 08:41
S60	0	jp-200345892\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 08:41
S61	2	jp-2003045892\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 08:41
S62	346	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 09:53
S63	325	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:54
S64	41	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:55
S65	7	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 10:19

S66	0	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft near4 polysilicon near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:56
S67	0	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft near10 polysilicon near10 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:56
S68	0	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft same polysilicon near10 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:56
S69	2	jp-2000058849\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 10:22
S70	2	jp-11307777\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 10:28
S71	2	jp-2003017502\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:14
S72	2	"20020195604".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 10:29
S73	8649	((257/59) or (257/72) or (257/270) or (257/346) or (257/351) or (257/355) or (257/356) or (257/387) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 12:40
S74	1420	S73 and (third three) near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 12:40

S75	657	S73 and (third three) near4 gate and (tft otft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 12:41
S76	2	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft) and 257/270:ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:16
S77	182	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft)"ti,ab,clm."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:17
S78	8	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab,clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:19
S79	0	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab,clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align) and low-voltage and high-voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:19
S80	6	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab,clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align) and ("low" adj voltage "lower" adj voltage low-voltage and "higher" adj voltage "high" adj voltage high-voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:20
S81	2	jp-05335573\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:27
S82	2	("5396084").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:42
S83	127	mondt.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:47

S84	462	(tft otft thin adj film adj transistor).ti,ab,clm. and (self-align\$2 self-alignment selfalign\$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:58
S85	440	(tft otft thin adj film adj transistor).ti,ab,clm. and (self-align\$2 self-alignment selfalign\$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:59
S86	307	(tft otft thin adj film adj transistor).ti,ab,clm. and (self-align\$2 self-alignment selfalign\$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker) near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:59
S87	278	(tft otft thin adj film adj transistor).ti,ab,clm. and (self-align\$2 self-alignment selfalign\$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker) near6 gate near6 (insulation insulating oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 15:00
S88	0	(additional second third separate) near4 gate.clm. and (low-voltage ("lower" "low") near2 voltage).clm. and (high-voltage ("higher" "high") near2 voltage).clm. and (thin adj film near2 transistor tft otft).clm. and (overlap overlapped overlaps overlapping).clm. and (self-align self-alignment self-aligned self-aligning).clm. and (thick thickness thicker).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 16:36
S89	2	jp-2000058849\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 17:10

S90	2	jp-11307777\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 17:08
S91	2	jp-2003017502\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 16:37
S92	2	"20020195604".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 17:10
S93	8	S89 S90 S91 S92	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 16:37
S94	2	("20030025127").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 16:59
S95	2	jp-2003017502\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/17 11:56